

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

2N681,A THRU 2N692,A

SILICON CONTROLLED RECTIFIER
25 AMPS, 25 THRU 800 VOLTS

JEDEC TO-48 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N681,A Series types are Silicon Controlled Rectifiers designed for phase control applications.

MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

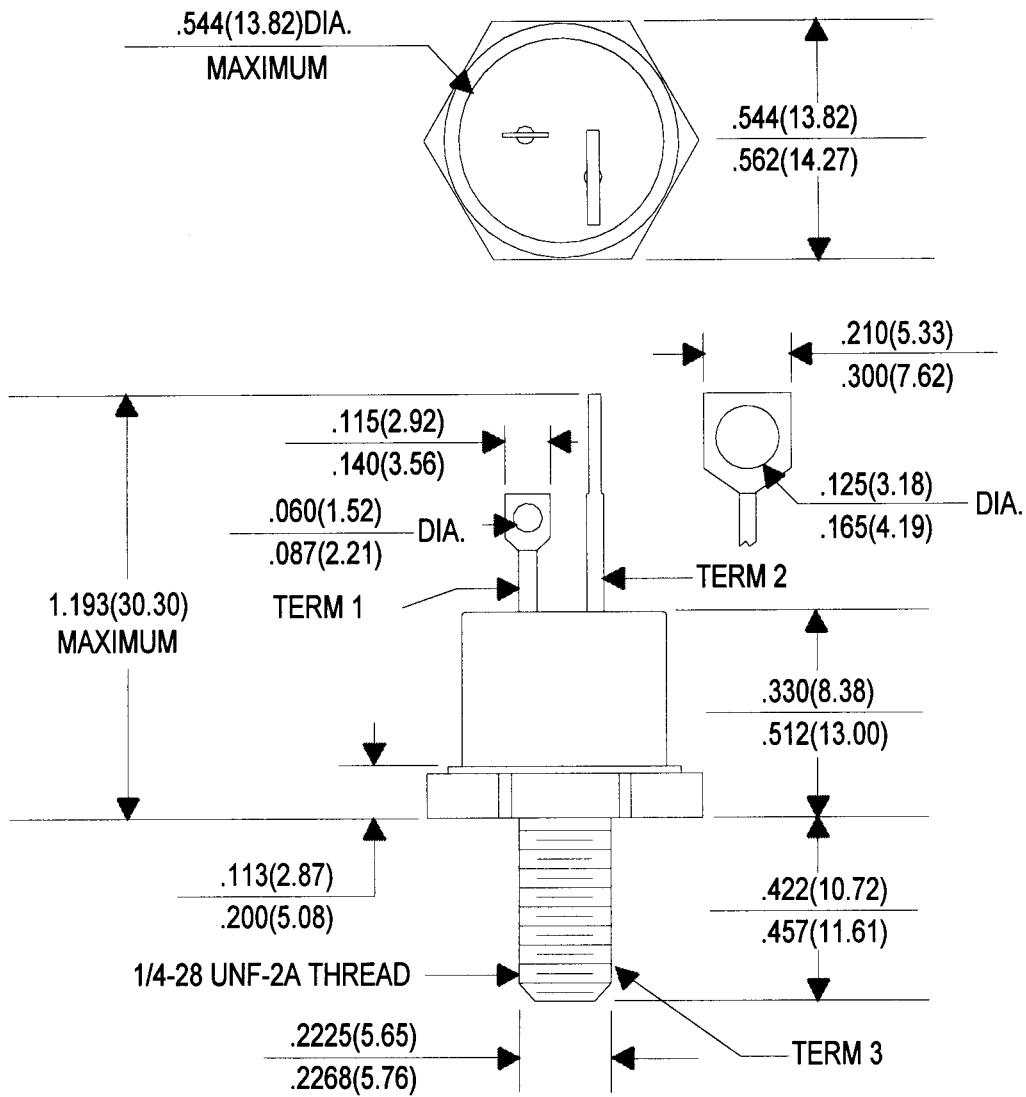
	2N681,A	2N682,A	2N683,A	2N684,A	2N685,A	2N686,A	2N687,A	2N688,A	2N689,A	2N690,A	2N691,A	2N692,A	UNITS	
V_{DRM}	25	50	100	150	200	250	300	400	500	600	700	800	V	
V_{RRM}	25	50	100	150	200	250	300	400	500	600	700	800	V	
V_{RSM}	25	50	100	150	200	250	300	400	500	600	700	800	V	
RMS On-State Current ($T_C=70^\circ\text{C}$)									$I_T(\text{RMS})$	25				A
Peak One Cycle Surge Current (60Hz)									I_{TSM}	200				A
Peak Gate Power Dissipation									P_{GM}	5.0				W
Average Gate Power Dissipation									$P_{G(AV)}$	0.5				W
Storage Temperature									T_{stg}	-65 to +150				$^\circ\text{C}$
Operating Junction Temperature									T_J	-65 to +125				$^\circ\text{C}$
Thermal Resistance, Junction to Case									θ_{JC}	1.5				$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N681,A, 2N682,A, 2N683, 2N684,A)			13	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N685,A)			12	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N686,A)			11	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N687,A)			10	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N688,A)			8.0	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N689,A)			6.0	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N690,A)			5.0	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N691,A)			4.5	mA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$ (2N692,A)			4.0	mA
I_{GT}	$V_D=12\text{V}, R_L=50\Omega$			40	mA
V_{GT}	$V_D=12\text{V}, R_L=50\Omega$			2.0	V
V_{TM}	$I_{TM}=50\text{A}, \text{PW}=1.0\text{ms}, \text{D.C}=2.0\%$			2.0	V
I_H	$V_D=7.0\text{V}, R_{GK}=1\text{K}\Omega$ (2N681 thru 2N692)			100	mA
I_H	$V_D=7.0\text{V}, R_{GK}=1\text{K}\Omega$ (2N681A thru 2N692A)			50	mA
dv/dt	Rated $V_{DRM}, T_C=125^\circ\text{C}$		100		V/ μs
t_{on}	$I_F=10\text{A}, I_G=200\text{mA}$		2.0		μs
t_{off}	$I_F=10\text{A}, I_G=200\text{mA}$		15		μs

(See Reverse Side)

JEDEC TO-48 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

LEAD CODE:

TERM 1) GATE
TERM 2) CATHODE
TERM 3) ANODE

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